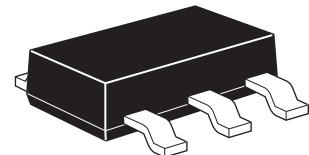


ZXMS6002G

60V N-Channel self protected enhancement mode IntelliFET™ MOSFET with status indication

Summary

Continuous drain source voltage	$V_{DS} = 60V$
On-state resistance	500mΩ
Nominal load current ($V_{IN} = 5V$)	1.4A
Clamping energy	550mJ

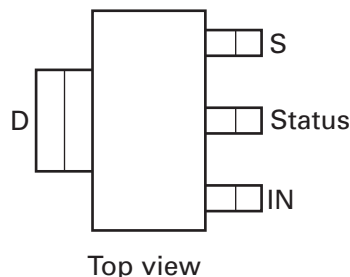


Description

Self protected low side MOSFET. Monolithic over temperature, over current, over voltage (active clamp) and ESD protected logic level functionality. Intended as a general purpose switch, with status indication.

Features

- Status pin (analog status indication)
- Short circuit protection with auto restart
- Over voltage protection (active clamp)
- Thermal shutdown with auto restart
- Over-current protection
- Input protection (ESD)
- Load dump protection (actively protects load)
- Logic level input
- High continuous current rating

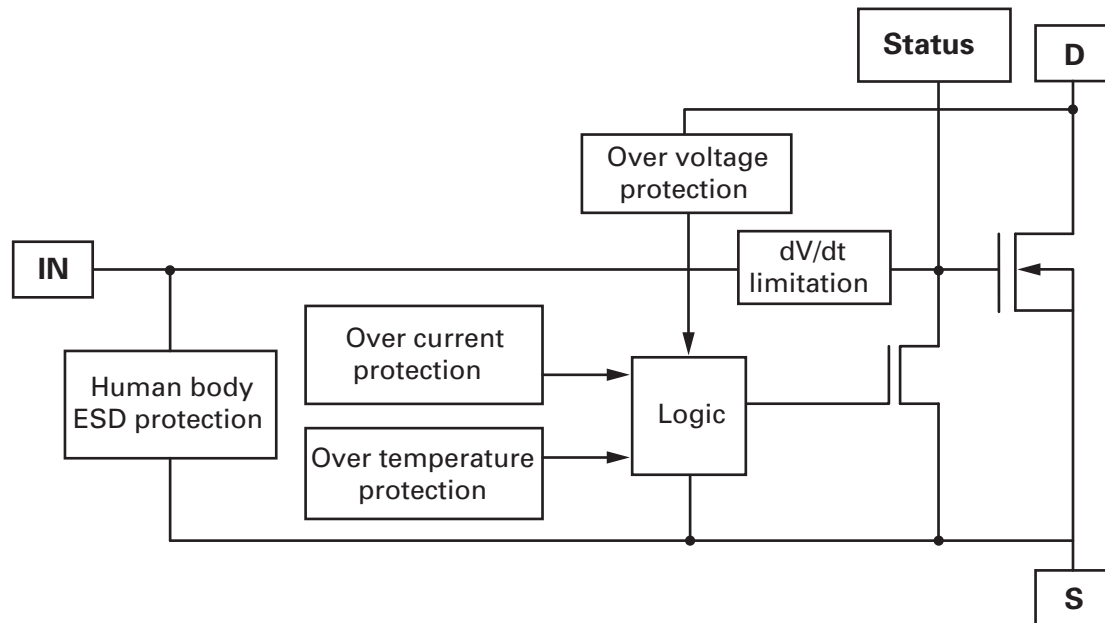


Note: The tab is connected to the drain pin and must be electrically isolated from the source pin. Connection of significant copper to the tab is recommended for best thermal performance.

Ordering information

Device	Part mark	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMS6002GTA	ZXMS6002	7	12 embossed	1000

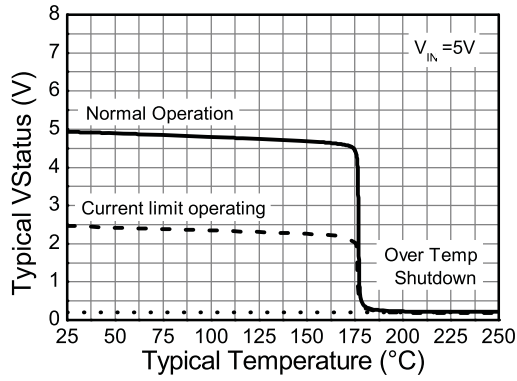
Functional block diagram



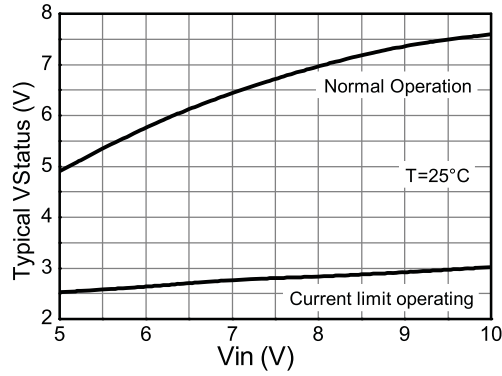
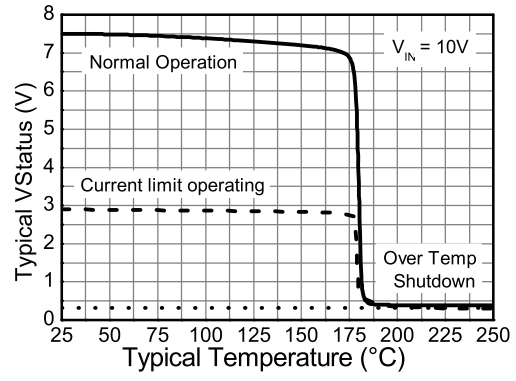
Applications and information

- Especially suited for loads with a high in-rush current such as lamps and motors
- All types of resistive, inductive and capacitive loads in switching applications
- μC compatible power switch for 12V and 24V DC applications
- Automotive rated
- Replaces electromechanical relays and discrete circuits
- Linear mode capability - the current-limiting protection circuitry is designed to de-activate at low V_{DS} , in order not to compromise the load current during normal operation. The design max. DC operating current is therefore determined by the thermal capability of the package/board combination, rather than by the protection circuitry
Note: This does not compromise the product's ability to self-protect during short-circuit load conditions.
- Status pin voltage reflects the gate drive being applied internally to the power MOSFET.
With $V_{\text{IN}} = 5\text{V}$:
Status voltage $\sim 5\text{V}$ indicates normal operation.
Status voltage $\sim (2-3)\text{V}$ indicates that the device is in current-limiting mode.
Status voltage $< 1\text{V}$ indicates that the device is in thermal shutdown.

Current Limiting and Over Temp Shutdown Status Indication at Vin=5V



Current Limiting and Over Temp Shutdown Status Indication at Vin=10V



VStatus vs Vin

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Continuous drain-source voltage	V_{DS}	60	V
Drain-source voltage for short circuit protection $V_{IN}=5V$	$V_{DS(SC)}$	36	V
Drain-source voltage for short circuit protection $V_{IN}=10V$	$V_{DS(SC)}$	20	V
Continuous input voltage	V_{IN}	-0.2 ... +10	V
Peak input voltage	V_{IN}	-0.2 ... +20	V
Operating temperature range	T_j	-40 to +150	°C
Storage temperature range	T_{stg}	-55 to +150	°C
Power dissipation @ $T_{amb}=25^{\circ}C^{(a)}$	P_D	2.5	W
Continuous drain current @ $V_{IN}=10V$; $T_{amb}=25^{\circ}C^{(a)}$	I_D	1.6	A
Continuous drain current @ $V_{IN}=5V$; $T_{amb}=25^{\circ}C^{(a)}$	I_D	1.4	A
Continuous source current (body diode) ^(a)	I_S	3	A
Pulsed source current (body diode) ^(b)	I_S	4.7	A
Unclamped single pulse inductive energy	E_{AS}	550	mJ
Load dump protection	$V_{LoadDump}$	80	V
Electrostatic discharge (human body model)	V_{ESD}	4000	V
DIN humidity category, DIN 40 040		E	
IEC climatic category, DIN IEC 68-1		40/150/56	

Thermal resistance

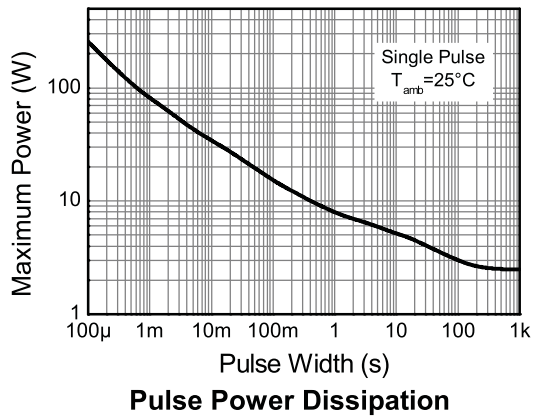
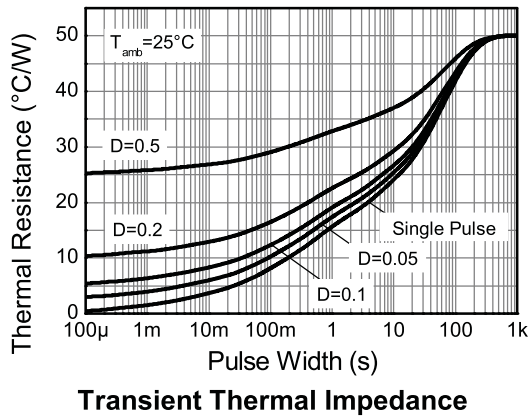
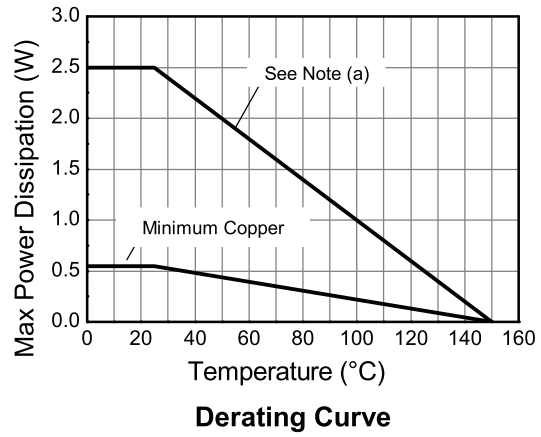
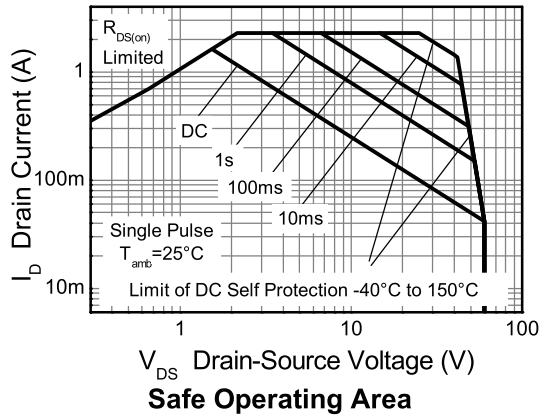
Parameter	Symbol	Limit	Unit
Junction to ambient ^(a)	$R_{\theta JA}$	50	°C/W
Junction to ambient ^(b)	$R_{\theta JA}$	28	°C/W

NOTES:

(a) For a device surface mounted on 50mm x 50mm x 1.6mm FR4 board with a high coverage of single sided 2oz weight copper.

(b) For a device surface mounted on FR4 board as (a) and measured at $t \leq 10s$.

Characteristics



ZXMS6002G

Electrical characteristics (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Static characteristics						
Drain-source clamp voltage	$V_{DS(AZ)}$	60	70	75	V	$I_D=10\text{mA}$
Off state drain current	I_{DSS}		0.1	3	μA	$V_{DS}=12\text{V}, V_{IN}=0\text{V}$
Off state drain current	I_{DSS}		3	15	μA	$V_{DS}=32\text{V}, V_{IN}=0\text{V}$
Input threshold voltage (*)	$V_{IN(th)}$	1	2.1		V	$V_{DS}=V_{GS}, I_D=1\text{mA}$
Input current	I_{IN}		0.7	1.2	mA	$V_{IN}=+5\text{V}$
Input current	I_{IN}		1.5	2.7	mA	$V_{IN}=+7\text{V}$
Input current	I_{IN}		4	7	mA	$V_{IN}=+10\text{V}$
Static drain-source on-state resistance	$R_{DS(on)}$		520	675	$\text{m}\Omega$	$V_{IN}=5\text{V}, I_D=0.7\text{A}$
Static drain-source on-state resistance	$R_{DS(on)}$		385	500	$\text{m}\Omega$	$V_{IN}=10\text{V}, I_D=0.7\text{A}$
Current limit (†)	$I_{D(LIM)}$	0.7	1.0	1.5	A	$V_{IN}=5\text{V}, V_{DS}>5\text{V}$
Current limit (†)	$I_{D(LIM)}$	1.0	1.8	2.3	A	$V_{IN}=10\text{V}, V_{DS}>5\text{V}$
Dynamic characteristics						
Turn-off time (V_{IN} to 90% I_D)	t_{off}		13	20	μs	$R_L=22\Omega, V_{IN}=10\text{V}$ to $0\text{V}, V_{DD}=12\text{V}$
Slew rate on (70 to 50% V_{DD})	$-dV_{DS}/dt_{on}$		8	20	$\text{V}/\mu\text{s}$	$R_L=22\Omega, V_{IN}=0$ to $10\text{V}, V_{DD}=12\text{V}$
Slew rate off (50 to 70% V_{DD})	dV_{DS}/dt_{on}		3.2	10	$\text{V}/\mu\text{s}$	$R_L=22\Omega, V_{IN}=10\text{V}$ to $0\text{V}, V_{DD}=12\text{V}$
Protection functions (‡)						
Required input voltage for over temperature protection	V_{PROT}	4.5			V	
Thermal overload trip temperature	T_{JT}	150	175		$^{\circ}\text{C}$	
Thermal hysteresis			1		$^{\circ}\text{C}$	
Unclamped single pulse inductive energy $T_j=25^{\circ}\text{C}$	E_{AS}	550			mJ	$I_{D(ISO)}=0.7\text{A}, V_{DD}=32\text{V}$
Unclamped single pulse inductive energy $T_j=150^{\circ}\text{C}$	E_{AS}	200			mJ	$I_{D(ISO)}=0.7\text{A}, V_{DD}=32\text{V}$

ZXMS6002G

Electrical characteristics (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Status flag						
Normal operation	V_{STATUS}		4.95		V	$V_{IN} = 5\text{V}$
Current limit operating	V_{STATUS}		2.5		V	$V_{IN} = 5\text{V}$
Thermal shutdown activated	V_{STATUS}		0.2	1	V	$V_{IN} = 5\text{V}$
Normal operation	V_{STATUS}		8.0		V	$V_{IN} = 10\text{V}$
Current limit operation	V_{STATUS}		3.0		V	$V_{IN} = 10\text{V}$
Thermal shutdown activated	V_{STATUS}		0.35	1	V	$V_{IN} = 10\text{V}$
Inverse diode						
Source drain voltage	V_{SD}			1	V	$V_{IN}=0\text{V}, -I_D=1.4\text{A},$

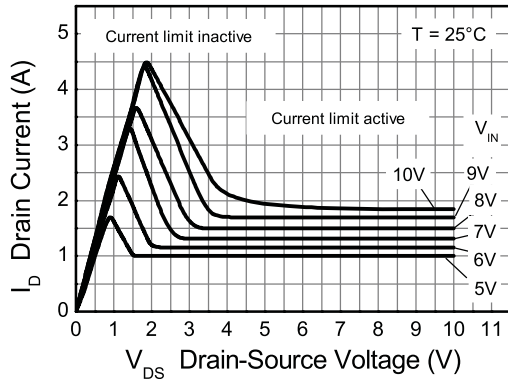
NOTES:

(*) Protection features may operate outside spec for $V_{IN}<4.5\text{V}$.

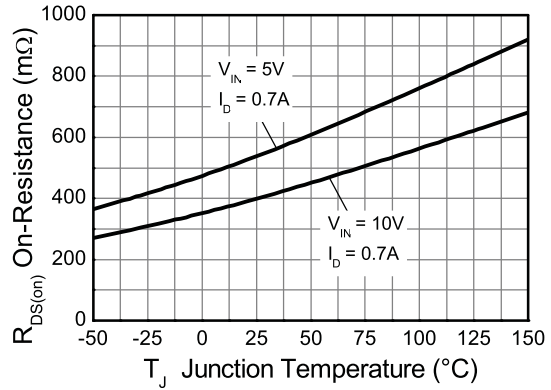
(†) The drain current is limited to a reduced value when V_{ds} exceeds a safe level

(‡) Integrated protection functions are designed to prevent IC destruction under fault conditions described in the datasheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous, repetitive operation.

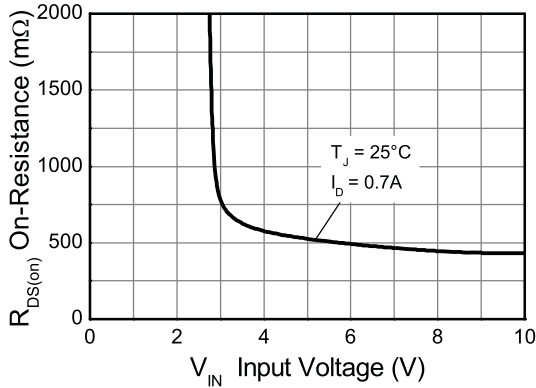
Typical characteristics



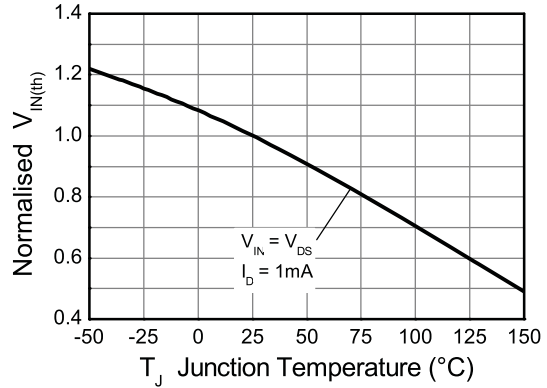
Typical Output Characteristic



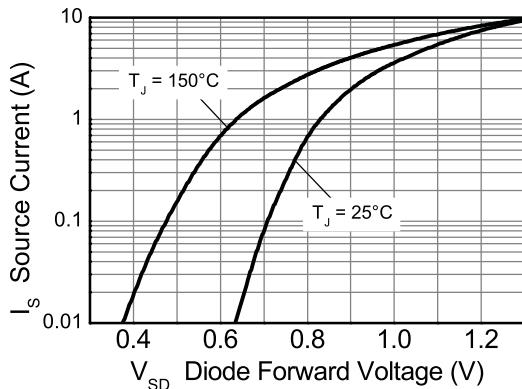
On-state Resistance vs Temperature



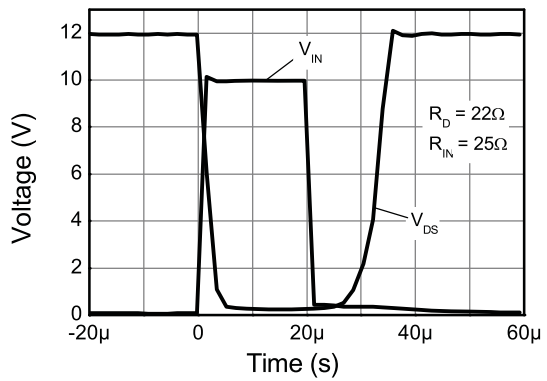
On-Resistance vs Input Voltage



Threshold Voltage vs Temperature



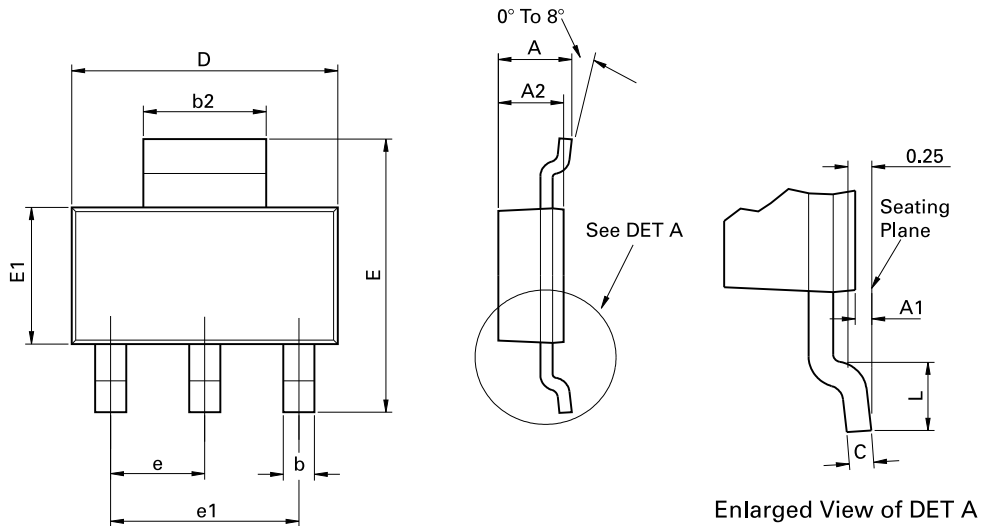
Source-Drain Diode Forward Voltage



Switching Speed

ZXMS6002G

Package outline - SOT223



Conforms to JEDEC TO-261 AA Issue B

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	-	1.80	-	0.071	e	2.30 BSC		0.0905 BSC	
A1	0.02	0.10	0.0008	0.004	e1	4.60 BSC		0.181 BSC	
b	0.66	0.84	0.026	0.033	E	6.70	7.30	0.264	0.287
b2	2.90	3.10	0.114	0.122	E1	3.30	3.70	0.130	0.146
C	0.23	0.33	0.009	0.013	L	0.90	-	0.355	-
D	6.30	6.70	0.248	0.264	-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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"Not recommended for new designs"	Device is still in production to support existing designs and production
"Obsolete"	Production has been discontinued

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